

Abstract of the Disclosure:

The capacitive electrode structure has a semiconductor substrate, a metal oxide layer on the semiconductor substrate, an oxidation inhibiting layer on the metal oxide layer, and an  
5 electrode formed on the oxidation inhibiting layer. The oxidation inhibiting layer is substantially impervious to oxygen and prevents oxygen atoms from diffusing into the metal oxide layer.

WHS:tk - 99p5363F//12/1/2000